

General Purpose Transistors

NPN Silicon

BCH817-16L/25L/40L, NSVBCH817-16L/25L/40L

Features

- 175°C T_{J(max)} Rated for High Temperature, Mission Critical Applications
- NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

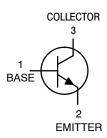
Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	45	V
Collector - Base Voltage	V_{CBO}	50	V
Emitter - Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I _C	500	mAdc
Collector Current - Peak	I _{CM}	1	Α

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	400	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	330	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.





SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



XXX = Device Code

M = Date Code*

• Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	-	-	-		
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	V _{(BR)CEO}	45	_	_	V
Collector – Emitter Breakdown Voltage (V _{EB} = 0, I _C = 10 μA)	V _{(BR)CES}	50	-	-	V
Emitter – Base Breakdown Voltage ($I_E = 1.0 \mu A$)	V _{(BR)EBO}	5.0	_	-	V
Collector Cutoff Current $(V_{CB} = 20 \text{ V})$ $(V_{CB} = 20 \text{ V}, T_A = 150^{\circ}\text{C})$	Ісво	- -	- -	100 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain $ \begin{array}{c} (I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}) \\ & BCH817-16, NSVBCH817-16 \\ BCH817-25, NSVBCH817-25 \\ BCH817-40, NSVBCH817-40 \\ \end{array} $	k	100 160 250 40	- - -	250 400 600 –	-
Collector – Emitter Saturation Voltage (I _C = 500 mA, I _B = 50 mA)	V _{CE(sat)}	-	_	0.7	V
Base – Emitter On Voltage (I _C = 500 mA, V _{CE} = 1.0 V)	V _{BE(on)}	-	_	1.2	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	100	_	_	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	10	_	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping [†]	
BCH817-16LT1G**	XXX	SOT-23	2000 / Tana & Baal	
NSVBCH817-16LT1G**	^^^	(Pb-Free)	3000 / Tape & Reel	
BCH817-25LT1G**	XXX	SOT-23	2000 / Tong & Floor	
NSVBCH817-25LT1G**	^^^	(Pb-Free)	3000 / Tape & Reel	
BCH817-40LT1G	ov.	SOT-23	0000 / Tong 9 Dool	
NSVBCH817-40LT1G	- 6X	(Pb-Free)	3000 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

^{**}Device release available upon request - Please contact onsemi sales.

TYPICAL CHARACTERISTICS - BCH817-16L, NSVBCH817-16L

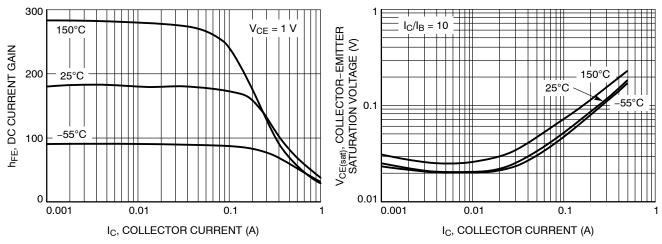


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

25°C

150°C

0.1

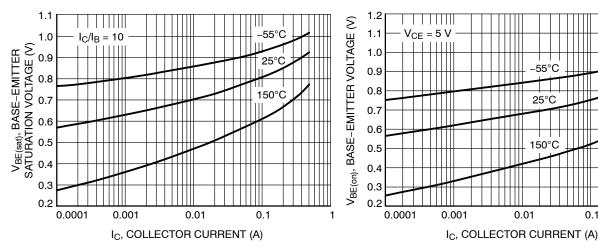
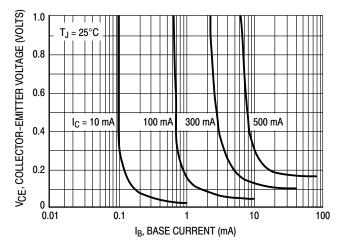


Figure 3. Base Emitter Saturation Voltage vs. **Collector Current**

Figure 4. Base Emitter Voltage vs. Collector Current

TYPICAL CHARACTERISTICS - BCH817-16L, NSVBCH817-16L



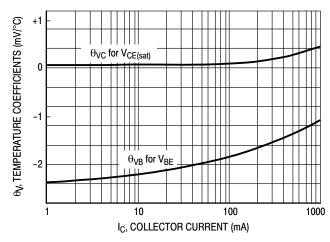


Figure 5. Saturation Region

Figure 6. Temperature Coefficients

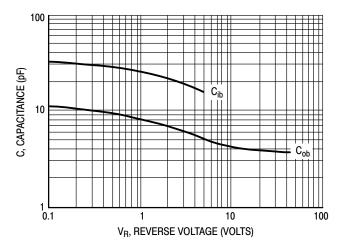


Figure 7. Capacitances

TYPICAL CHARACTERISTICS - BCH817-25L, NSVBCH817-25L

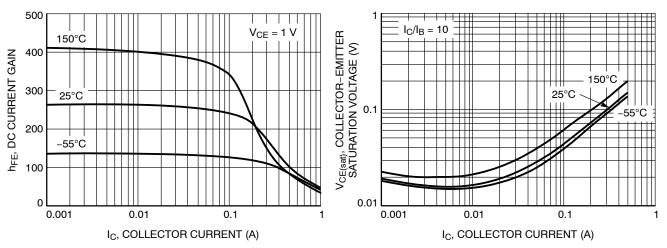


Figure 8. DC Current Gain vs. Collector Current

Figure 9. Collector Emitter Saturation Voltage vs. Collector Current

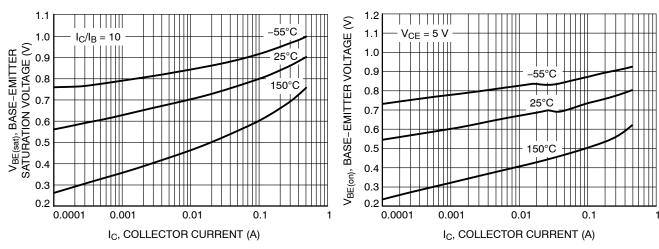


Figure 10. Base Emitter Saturation Voltage vs.
Collector Current

Figure 11. Base Emitter Voltage vs. Collector Current

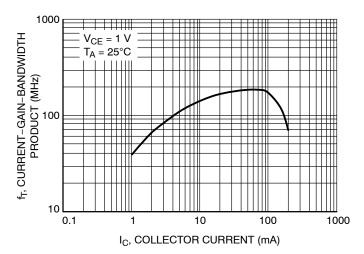
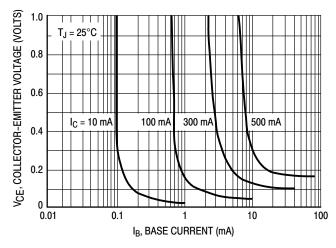


Figure 12. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BCH817-25L, NSVBCH81725L



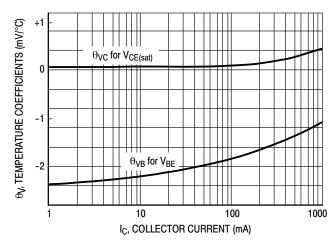


Figure 13. Saturation Region

Figure 14. Temperature Coefficients

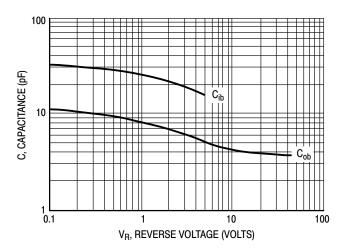


Figure 15. Capacitances

TYPICAL CHARACTERISTICS - BCH817-40L, NSVBCH817-40L

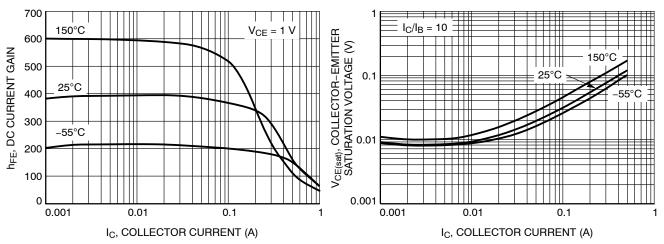


Figure 16. DC Current Gain vs. Collector Current

Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

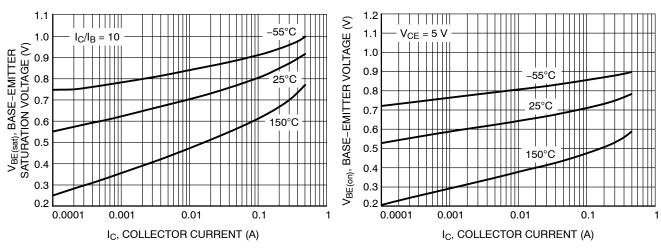


Figure 18. Base Emitter Saturation Voltage vs. Collector Current

Figure 19. Base Emitter Voltage vs. Collector Current

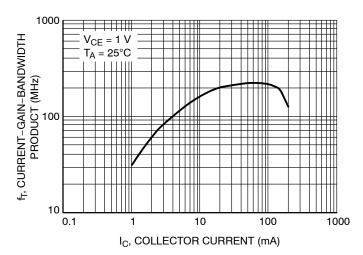
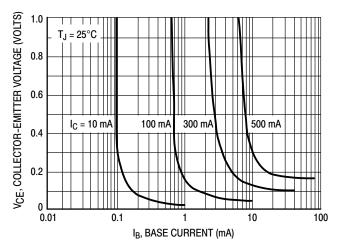


Figure 20. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BCH817-40L, NSVBCH817-40L



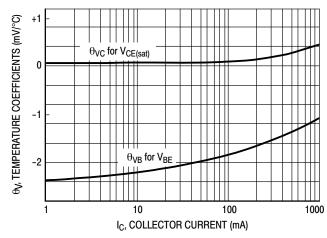


Figure 21. Saturation Region

Figure 22. Temperature Coefficients

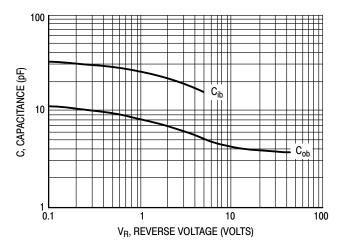


Figure 23. Capacitances

TYPICAL CHARACTERISTICS – BCH817–16L, NSVBCH817–16L, BCH817–25L, NSVBCH817–25L, BCH817–40L, NSVBCH817–40L

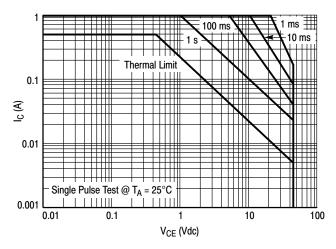


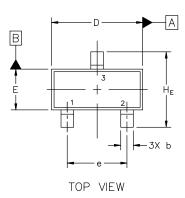
Figure 24. Safe Operating Area

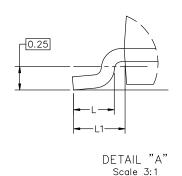


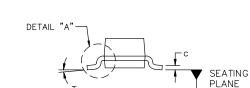


SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

DATE 14 AUG 2024







END VIEW



NOTES:

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



SIDE VIEW

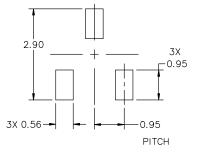


XXX = Specific Device Code

= Date Code

= Pb-Free Package

^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



C

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	N	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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